

Express Mail No. EV 346 811 096 US

THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Bruno GHYSELEN et al.

Confirmation No. 2494

Application No.: 10/784,016

Group Art Unit: 2811

Filing Date: February 20, 2004

Examiner:

For: FORMING STRUCTURES THAT INCLUDE A
RELAXED OR PSEUDO-RELAXED LAYER ON
A SUBSTRATE

Atty. Docket No.: 4717-10000

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Pursuant to applicant's duty of disclosure under 37 C.F.R. 1.56, applicants submit herewith (8) references for the Examiner's review and consideration. These references are discussed in the specification and are listed on the enclosed Form PTO-1449. It is respectfully requested that these references be made of record in this application by the Examiner's completion and return of the Form PTO-1449.

No fee is believed to be due for the filing of this statement as it is being submitted prior to an initial office action for this application. Should any fees be required, however, please charge such fees to Winston & Strawn LLP Deposit Account No. 50-1814.

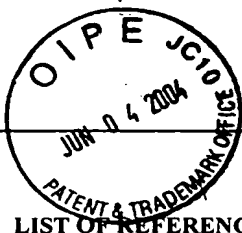
Respectfully submitted,

Date: June 3, 2004

Allan A. Fanucci (Reg. No. 30,256)

WINSTON & STRAWN LLP
CUSTOMER NO. 28765
(212) 294-3311

Enclosures



LIST OF REFERENCES CITED BY APPLICANT <i>(Use several sheets if necessary)</i>	ATTY. DOCKET NO.:	APPLICATION NO.:
	4717-10000	10/784,016
	APPLICANT:	
	Bruno GHYSELEN et al.	
	FILING DATE:	GROUP:
	February 20, 2004	2811

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	AA	5,461,243	10/1995	Ek et al.	257	190	
	AB	6,352,942 B1	3/2002	Luan et al.	438	770	
	AC	6,100,166	8/2000	Sakaguchi et al.	438	455	
	AD						
	AE						
	AF						
	AG						
	AI						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	AJ							
	AK							
	AL							

OTHER REFERENCES *(Including Author, Title, Date, Pertinent Pages, Etc.)*

	AM	B. Holländer et al., "Strain relaxation of pseudomorphic Si _{1-x} Ge _x /Si(100) heterostructures after hydrogen or helium ion implantation for virtual substrate fabrication", Nuclear Instruments and Methods in Physics Research B 175-177 (2001) 357-367 (2001)
	AN	K.D. Hobart et al. "Complaint Substrates: A Comparative Study of the Relaxation Mechanisms of Strained Films Bonded to High and Low Viscosity Oxides", Electronic Materials, Vol. 29, No. 7, pp. 897-900 (2000)
	AO	Friedrich Schäffler, "High-mobility Si and Ge structures", Semicond. Sci. Technol., Vol. 12, pp.1515-1548 (1997)
	AP	Q. Y. Tong et al "Extracts of "Semi-conductor on wafer bonding", Science and Technology, Interscience Technology, Wiley Interscience publication, Johnson Wiley & Sons, Inc.
	AQ	J.P. Collinge, "Silicon-on-insulator technology", Materials to VLSI, 2nd Edition", Kluwer Academic Publisher, pp. 50-51.

EXAMINER	DATE CONSIDERED
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.